

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTORNEY DOCKET NO. 10003976-4	SERIAL NO. TBA
APPLICANT Moll et al.	
FILING DATE TBA	GROUP TBA

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME
DP	AA 6,388,307	05/14/02	Kondo et al.
DF	AB 2002/0027232 A1	03/07/02	Shigematsu et al.
DF	AC 6,339,233	01/15/02	Lell
DF	AD 6,316,795	11/13/01	Croke, III
PF	AE 6,251,738	06/26/01	Huang
DF	AF 5,387,808	02/07/95	Nozu
DF	AG 5,349,201	09/20/94	Stanchina et al.
DF	AH 4,821,082	04/11/89	Frank et al.

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	TRANSLATION YES NO
DF	BA	EPO-0571994A2	05/27/93	Stanchina, William E.	X
DF	BB	JP-6-224230	08/12/94	Yashiki et al.	X
DF	BC	WO 01/09957 A1	02/08/01	Micovic, Miroslav	X

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

DF	CA	Bell Telephone Laboratories, Inc., <i>Semiconductor Device, Physics and Technology</i> , S.M. SZE, AT&T <i>Bell Laboratories</i> , 1985, (267-269)
DF	CB	G.J. Sullivan, et al., <i>MBE Growth and Characterization of High Gain AlGaAs/GaAsSb/GaAs NpN HBTs</i> , <i>Inst. Phys. Conf. Ser. No. 120: Chapter 13</i> , 1991 (647-650)
DF	CC	N. Matine, et al., <i>Electrical Stress Damage Reversed In Non-Passivated Fully Self-Aligned InP HBTs By Ozone Surface Treatment</i> , <i>Electronics Letters</i> , December 9, 1999, Vol. 35, No. 25
DF	CD	C.R. Bolognesi, et al., <i>High Performance InP/GaAsSb/InP DHBTs With Heavily Doped Base Layers</i> , 2000 <i>IEEE</i> , (12-18)
DF	CE	S.P. Watkins, et al., <i>Heavily Carbon-Doped GaAsSb Grown on InP For HBT Applications</i> , <i>Journal of Crystal Growth</i> 221 (2000) (59-65)
DF	CF	M.W. Dvorak, et al. <i>Abrupt Junction InP/GaAsSb/InP Double Heterojunction Bipolar Transistors With F₁ as High As 250 GHz and B_V _{CEO} > 6V</i> , 2000 <i>IEEE</i> (178-181)
DF	CG	Tohru Oka, et al. <i>Low Turn-on Voltage GaAs Heterojunction Bipolar Transistors With a Pseudomorphic GaAsSb Base</i> , <i>Applied Physics Letters</i> , Vol 78, No. 4, 2001, (483485)
DF	CH	M.W. Dvorak, et al., <i>MOCVD-Grown 175 GHz InP/GaAs_{1-x}Sb_x/InP DHBTs With High Current Gains Using Strained and Heavily C-Doped Base Layers</i>

EXAMINER

DATE CONSIDERED

11/21/05

* Copies of these references are not enclosed Pursuant to 37 CFR 1.98(d). (See accompanying IDS)